

第104回半導体表面化学セミナー

(尾嶋研セミナー)

104th Semiconductor Surface Chemistry Seminar

(Oshima Lab Seminar)



1. 日時:平成25年2月28日(木)午後3時~4時半
2. 場所:本郷キャンパス工学部5号館第2輪講室(541号室)
3. 講師:Stefan Heun氏(NEST, Istituto Nanoscienze-CNR and Scuola Normale Superiore, Pisa, Italy)
4. タイトル:「STM studies of Hydrogen on Graphene」

概要

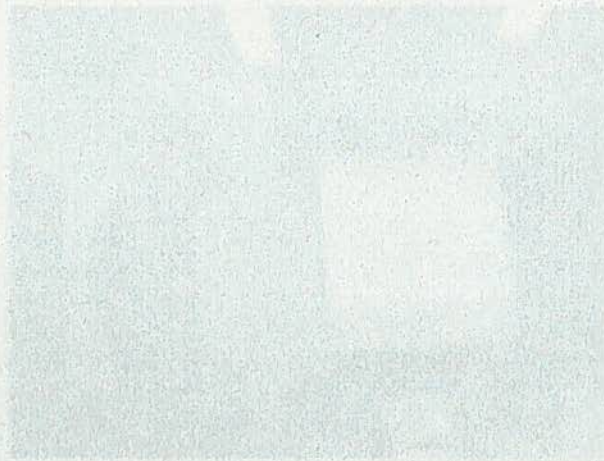
The realization of new and innovative hydrogen storage materials has worldwide strategic importance. In this context, graphene has recently attracted attention as a promising hydrogen storage medium. Indeed, graphene is lightweight, chemically stable, and exhibits attractive physico-chemical properties for hydrogen adsorption. Furthermore, the interaction between hydrogen and graphene can be controlled by chemical functionalization of the material, thus enabling fine tuning of the adsorption/desorption-properties of hydrogen on graphene. Theoretical studies suggest that graphene can adsorb up to 8 wt% by chemisorption and up to 10 wt% by physisorption of hydrogen. However, experimental demonstrations of these numbers have yet to be reported. The energetics of the chemisorption of hydrogen on graphene can be modified by the local curvature of the graphene sheet. This effect is proposed as the basis of hydrogen storage systems in which the storage and release of hydrogen are obtained by exploiting and controlling the corrugation of individual layers of graphene. Testing these predictions we performed scanning tunneling microscopy experiments of hydrogenated graphene grown on SiC(0001). For the first time, we atomically resolved the hexagonal lattice of the buffer layer verifying that it is topologically identical to graphene [1]. We studied the positions of the hydrogen atoms on the atomically resolved lattice of monolayer graphene as a function of curvature by hydrogenating the sample in situ. We found that atomic hydrogen binds to the carbon atoms in the convexly curved areas of the supercell, indicating a $\sim 0.15\text{eV}$ increase in the binding energy as compared to flat graphene (0.7eV). We measured the carbon-hydrogen bond height to be $\sim 1\text{\AA}$, close to the calculated bond length of 1.1\AA . Theoretical studies regarding metal atoms (e.g. Ti) deposited on graphene suggest that such materials can adsorb up to 10 wt% gravimetric density of hydrogen. Each adsorbed Ti atom is predicted bind up to 4 \sim 5 H_2 molecules. Given the large number of theoretical papers on this subject, it is surprising that experimental demonstrations of the effect of such modifications on graphene have yet to be reported. Experimental work is under way in our group in order to evaluate the

feasibility of graphene as a hydrogen storage medium. We have first experimental evidence that Ti atoms can store hydrogen molecules and release them at around 250 ° C. [1]S. Goler, C. Coletti, V. Piazza, P. Pingue, F. Colangelo, V. Pellegrini, K. V. Emtsev, S. Forti, U. Starke, F. Beltram, and S. Heun, Carbon 51, 249 (2013).

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104th Semiconductor Surface Chemistry Seminar

(Oshima Lab Seminar)



1. 日時: 平成25年2月28日(木)午後3時~5時半
2. 場所: 本館1F 応用理工学館3号館2階演習室(551号室)
3. 講師: Simon Goler (MIT, Istituto Nazionale CNR and Santa Normala Superiore, Pava, Italy)
4. タイトル: STM study of hydrogen on Graphene

概要

The realization of solid state hydrogen storage molecules has worldwide strategic importance. As such, carbon nanotubes has recently attracted attention as promising hydrogen storage medium because of their high weight, chemically stable, and possible alternative physical chemical processes for hydrogen adsorption. Furthermore, the interaction between hydrogen and graphene may be controlled by chemical functionalization of the material that covering the surface of the molecule. We study the adsorption properties of hydrogen on graphene. Theoretical studies suggest that hydrogen can adsorb up to 6 atoms by chemisorption and up to 10 with physisorption on hydrogen, however, experimental demonstrations of these numbers have yet to be reported. The adsorption of the hydrogen atoms on graphene can be modified by the local curvature of the carbon network. The effect is probed as the result of hydrogen atomic spin-orbit coupling. We study the adsorption of hydrogen on graphene by separating the adsorption of hydrogen on graphene. To study these properties we perform scanning tunneling spectroscopy experiments of hydrogenated graphene grown on SiC(0001). For the hydrogen, we experimentally observed the hydrogen binding at the buffer layer, verifying that it is the hydrogen, attached to graphene. [1]. We studied the positions of the hydrogen atoms on the atomically resolved surface of monolayer graphene as a function of coverage by investigating the surface spin-orbit. We found the atomic hydrogen binds to the carbon atoms in the negatively charged areas of the surface, indicating a 0.18eV increase in the binding energy as compared to flat graphene (0.74eV). We measured the vertical hydrogen bond height to be 0.24 Å close to the calculated bond length of 0.18 Å. Theoretical studies regarding carbon atoms (e.g. Ti) deposited on graphene suggest that such materials can adsorb up to 10 wt% hydrogen, double of hydrogen. Each adsorbed Ti atom is predicted bind up to 4-5 H₂ molecules. Given the large number of theoretical papers in this subject, it is surprising that experimental demonstrations of the effect of such modification on graphene have yet to be reported. Experimental work is under way in our group in order to evaluate the